



Docket No.: 02SPE113P-DIV2

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Hsia, et al.

Serial No.: 09/955,677

Filed: September 19, 2001

For: Method and Apparatus for High-Resolution In-Situ Plasma Etching of **Inorganic and Metal Films** 

Art Unit: 2822

Examiner: Ida M. Soward

## AMENDMENT AND RESPONSE TO OFFICE ACTION

Honorable Commissioner of Patents and Trademarks Washington, D.C. 20231

Dear Sir/Madam:

rable Commissioner of ts and Trademarks ington, D.C. 20231

Sir/Madam:

Technology CEX 15 2002

Sir/Madam:

This is in response to the Office Action dated September 26, 2002 in the abovereferenced patent application. Please enter and consider the following amendments and remarks.

Please change the Attorney Docket No. in this application from "050324-1141" to --02SPE113P-DIV2--.